Ordering number:EN462E

NPN Epitaxial Planar Silicon Transistor

2SC2078

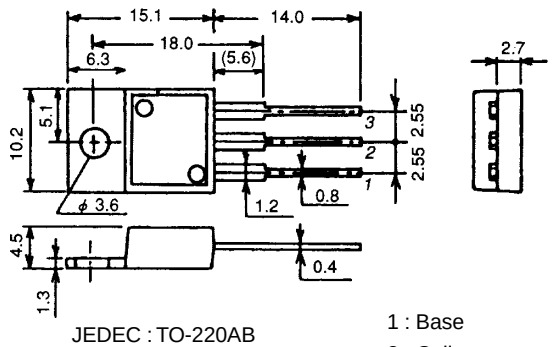
27MHz RF Power Amplifier Applications

Package Dimensions

unit:mm

2010C

[2SC2078]



JEDEC : TO-220AB
EIAJ : SC-46

1 : Base
2 : Collector
3 : Emitter

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		80	V
Collector-to-Emitter Voltage	V_{CER}	R_{BE}=150Ω	75	V
Emitter-to-Base Voltage	V_{EBO}		5	V
Collector Current	I_C		3	A
Collector Current (Pulse)	I_{CP}		5	A
Collector Dissipation	P_C		1.2	W
		Tc=50˚C	10	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=40V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0			10	μA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=0.5A	25*		200*	
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=0.1A	100	150		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz		45	60	pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=1A, I_B=0.1A		0.15	0.6	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=1A, I_B=0.1A		0.9	1.2	V

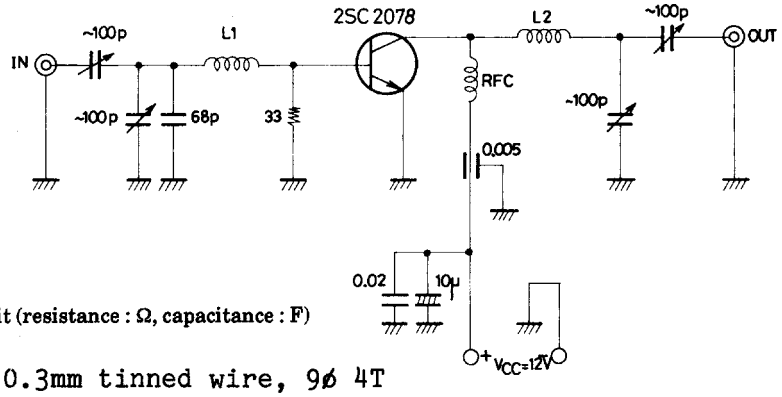
* : The 2SC2078 are classified by 0.5A h_{FE} as follows :

25	B	50	40	C	80	60	D	120	100	E	200

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

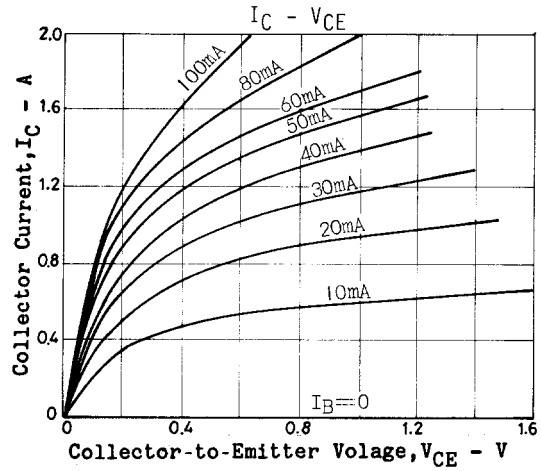
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Saturation Voltage	$V_{(BR)CBO}$	I_C=100μA, I_B=0	80			V
Collector-to-Emitter Saturation Voltage	$V_{(BR)CER}$	I_C=1mA, R_{BE}=150Ω	75			V
Emitter-to-Base Saturation Voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
[At specified test circuit]						
Output Power	P_O	V_{CC}=12V, f=27MHz, Pi=0.2W	4.0			W
Power Efficiency	η		60			%

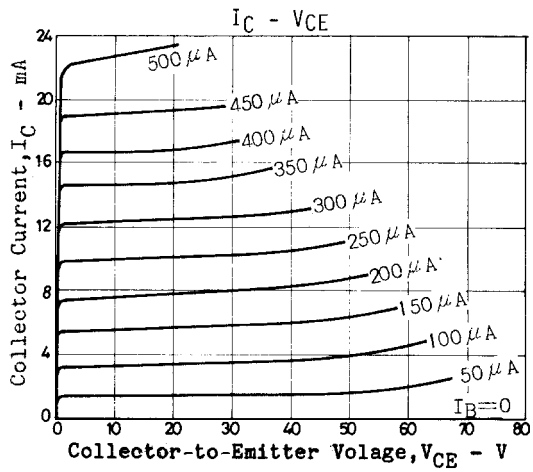
27MHz Output Power Test Circuit

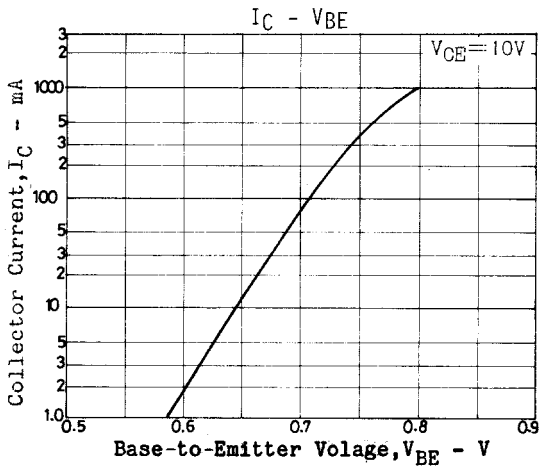


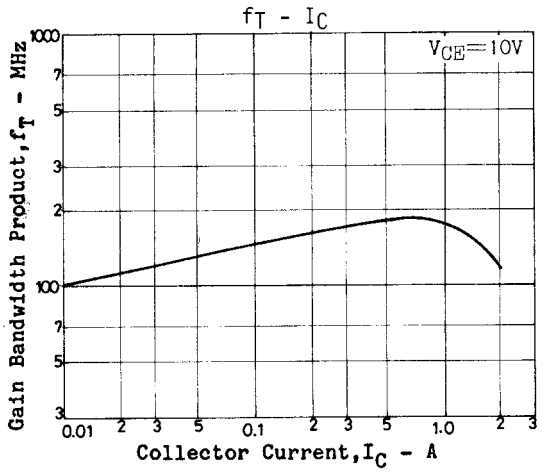
Unit (resistance : Ω, capacitance : F)

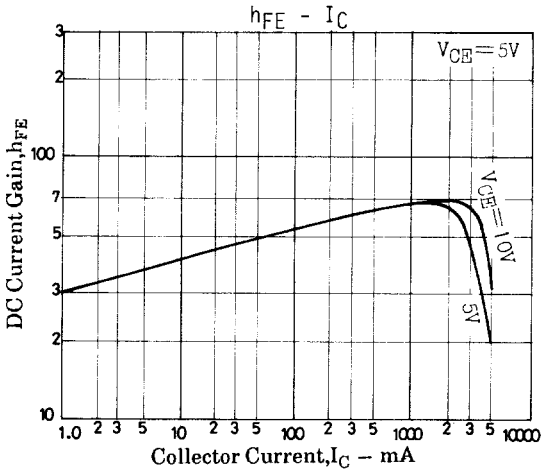
Coil data L1: 0.3mm tinned wire, 9ø 4T
L2: 0.6mm tinned wire, 9ø 4T
RFC 2.2μH

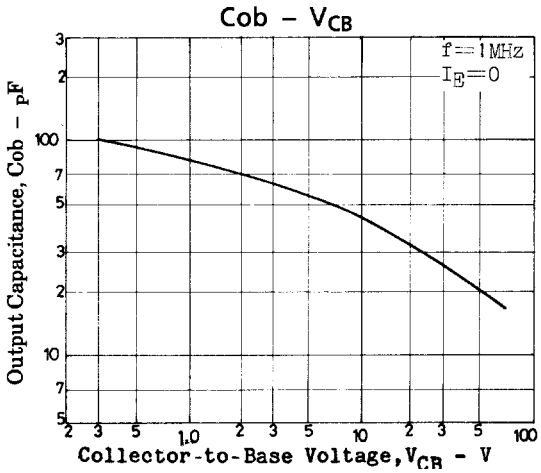


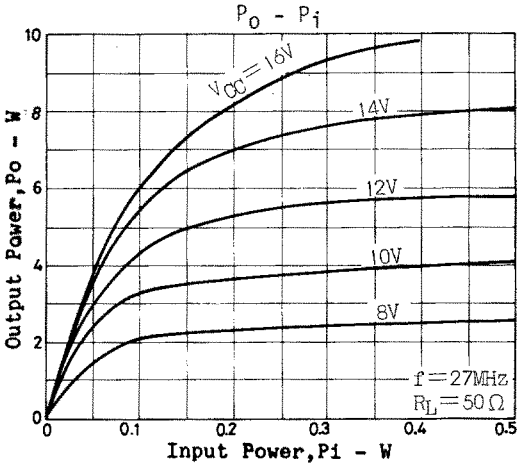


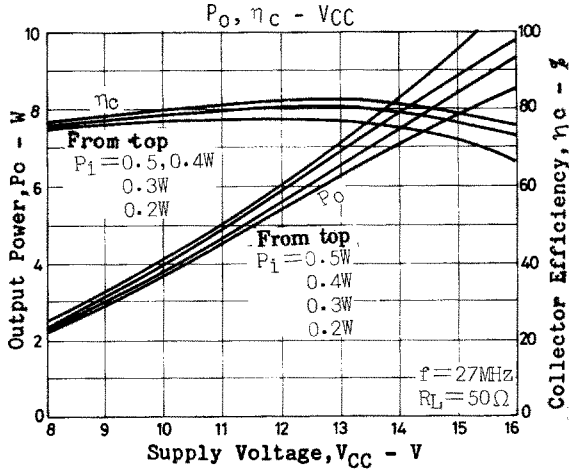


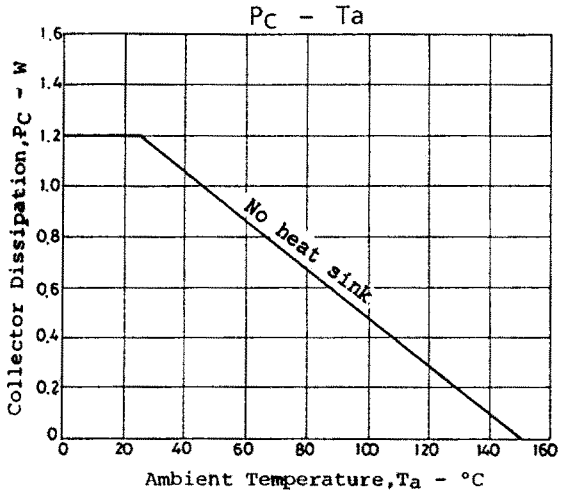


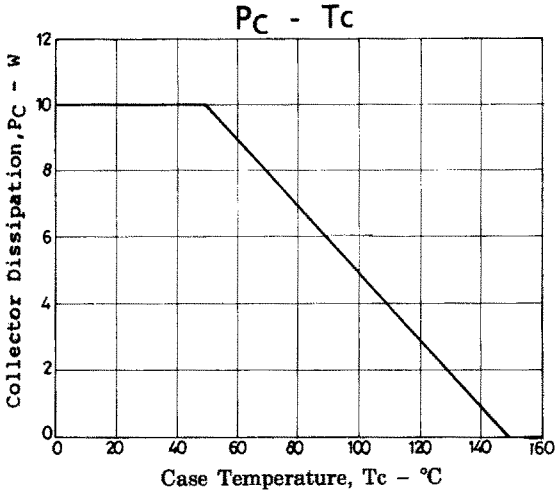

hFE - IC
VCE=5V
VCE=10V
5V
DC Current Gain,hFE
Collector Current,IC – mA


Cob – VCB
f=1MHz
IE=0
Output Capacitance, Cob – pF
Collector-to-Base Voltage,VCB - V


Po - Pi
VCC=16V
14V
12V
10V
8V
f=27MHz
RL=50Ω
Output Power,Po - W
Input Power,Pi - W


Po, ηc - VCC
ηc
From top
Pi=0.5,0.4W
0.3W
0.2W
Po
From top
Pi=0.5W
0.4W
0.3W
0.2W
f=27MHz
RL=50Ω
Output Power,Po - W
Collector Efficiency, ηc - %
Supply Voltage,VCC - V


PC - Ta
No heat sink.
Collector Dissipation,PC - W
Ambient Temperature,Ta - °C


PC - Tc
Collector Dissipation,PC - W
Case Temperature, Tc – °C